# **2SB0779** (2SB779)

## Silicon PNP epitaxial planar type

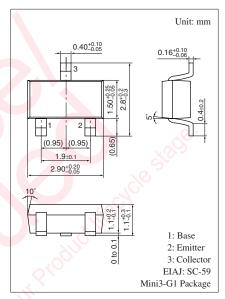
#### For low-frequency output amplification

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- ullet Satisfactory linearity of forward current transfer ratio  $h_{FE}$  at the low collector voltage
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

## ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	-25	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-20	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V	
Collector current	$I_{C}$	-500	mA	
Peak collector current	I <sub>CP</sub>	-1	A	
Collector power dissipation	P <sub>C</sub>	200	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



Marking Symbol: 1A

## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A},  I_E = 0$	-25	35		V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-20			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -25 \text{ V}, I_E = 0$			-100	nA
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -20 \text{ V}, I_B = 0$			-1	μΑ
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	90		220	_
	h <sub>FE2</sub>	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	25			_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.4	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1.2	V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		15		pF
(Common-emitter reverse transfer)						

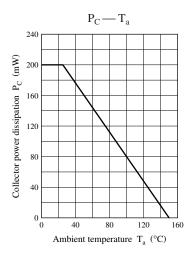
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

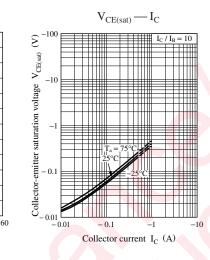
#### 2. \*1: Pulse measurement

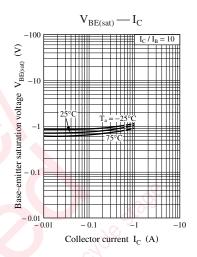
#### \*2: Rank classification

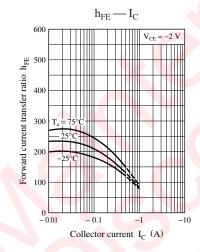
Rank	Q	R
$h_{FE1}$	90 to 155	130 to 220

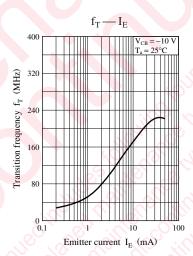
Note) The part number in the parenthesis shows conventional part number.

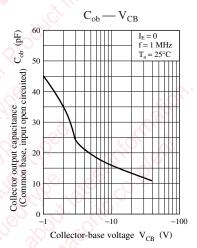












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